

Nattapol Damrongplasit

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Threshold Voltage and DIBL Variability Modeling Based on Forward and Reverse Measurements for SRAM and Analog MOSFETs. IEEE Transactions on Electron Devices, 2015, 62, 1119-1126.	3.0	8
2	Comparison of 10 nm GAA vs. FinFET 6-T SRAM performance and yield. , 2014, , .		2
3	Oxygen-inserted SegFET: A candidate for 10-nm node system-on-chip applications. , 2014, , .		0
4	Variation-Aware Comparative Study of 10-nm GAA Versus FinFET 6-T SRAM Performance and Yield. IEEE Transactions on Electron Devices, 2014, 61, 3949-3954.	3.0	15
5	Extension of Planar Bulk n-Channel MOSFET Scaling With Oxygen Insertion Technology. IEEE Transactions on Electron Devices, 2014, 61, 3345-3349.	3.0	11
6	Design of Gate-All-Around Silicon MOSFETs for 6-T SRAM Area Efficiency and Yield. IEEE Transactions on Electron Devices, 2014, 61, 2371-2377.	3.0	16
7	4H-SiC N-Channel JFET for Operation in High-Temperature Environments. IEEE Journal of the Electron Devices Society, 2014, 2, 164-167.	2.1	26
8	Comparative Study of Uniform Versus Supersteep Retrograde MOSFET Channel Doping and Implications for 6-T SRAM Yield. IEEE Transactions on Electron Devices, 2013, 60, 1790-1793.	3.0	15
9	Impact of Gate Line-Edge Roughness (LER) Versus Random Dopant Fluctuations (RDF) on Germanium-Source Tunnel FET Performance. IEEE Nanotechnology Magazine, 2013, 12, 1061-1067.	2.0	14
10	Study of Random Dopant Fluctuation Induced Variability in the Raised-Ge-Source TFET. IEEE Electron Device Letters, 2013, 34, 184-186.	3.9	124
11	6-T SRAM cell design with gate-all-around silicon nanowire MOSFETs. , 2013, , .		5
12	Performance and Yield Benefits of Quasi-Planar Bulk CMOS Technology for 6-T SRAM at the 22-nm Node. IEEE Transactions on Electron Devices, 2011, 58, 1846-1854.	3.0	23
13	Variation Study of the Planar Ground-Plane Bulk MOSFET, SOI FinFET, and Trigate Bulk MOSFET Designs. IEEE Transactions on Electron Devices, 2011, 58, 3294-3299.	3.0	55
14	Study of Random Dopant Fluctuation Effects in Germanium-Source Tunnel FETs. IEEE Transactions on Electron Devices, 2011, 58, 3541-3548.	3.0	149